

AMENDMENTS IN THE CLAIMS:

1. (Original) A method of growing a p-type nitride semiconductor material by molecular beam epitaxy, the method comprising supplying bis(cyclopentadienyl)magnesium (Cp_2Mg) during the growth process.
2. (Original) A method as claimed in claim 1 wherein the nitride semiconductor material is p-type (Ga,Al)N.
3. (Currently Amended) A method as claimed in claim 1 ~~or 2~~ and comprising supplying ammonia gas during the growth process.
4. (Currently Amended) A method as claimed in claim 1, ~~2 or 3~~ and comprising supplying ammonia gas, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type GaN.
5. (Currently Amended) A method as claimed in claim 1, ~~2 or 3~~ and comprising supplying ammonia gas, aluminium, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type AlGaN.
6. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1, and comprising changing the supply rate of Cp_2Mg during the growth of the nitride semiconductor material.
7. (Cancelled)
8. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 wherein the growth process is carried out at a temperature of at least 800°C .
9. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 wherein the growth process is carried out at a temperature of at least 850°C .

10. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 wherein the growth process is carried out at a temperature of at least 920°C.

11. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 wherein the growth process is carried out at a temperature of at least 950°C.

12. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 wherein the growth process is carried out at a temperature of 960°C or below.

13. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 and comprising supplying Cp_2Mg at a beam equivalent pressure of at least 1×10^{-9} mbar.

14. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 and comprising supplying Cp_2Mg at a beam equivalent pressure of at least 3×10^{-9} mbar.

15. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 and comprising supplying Cp_2Mg at a beam equivalent pressure of 1×10^{-7} mbar or below.

16. (Currently Amended) A method as claimed in ~~any preceding~~ claim 1 and comprising supplying Cp_2Mg at a beam equivalent pressure of 1.5×10^{-8} mbar or below.

17. (Currently Amended) A method as claimed in claim 4, ~~or in any of claims 6 to 16 when dependent from claim 4~~, and comprising supplying elemental gallium at a beam equivalent pressure of at least 1×10^{-8} mbar.

18. (Currently Amended) A method as claimed in claim 4, ~~or in any of claims 6 to 16 when dependent from claim 4~~, and comprising supplying elemental gallium at a beam equivalent pressure of 1×10^{-5} mbar or below.

19. (Currently Amended) A method as claimed in claim 5, ~~or in any of claims 6 to 16 when dependent from claim 5~~, and comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of at least 1×10^{-8} mbar.
20. (Currently Amended) A method as claimed in claim 5, ~~or in any of claims 6 to 16 when dependent from claim 5~~, and comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of 1×10^{-5} mbar or below.
21. (Currently Amended) A p-type nitride semiconductor material grown by a method defined in claim 1 ~~any of claims 1 to 20~~.
22. (Currently Amended) A semiconductor device comprising a layer of a p-type nitride semiconductor material grown by a method defined in claim 1 ~~any of claims 1 to 24~~.
23. (Original) A semiconductor device as claimed in claim 22 wherein the layer of nitride semiconductor material is a layer of p-type (Ga,Al)N.